

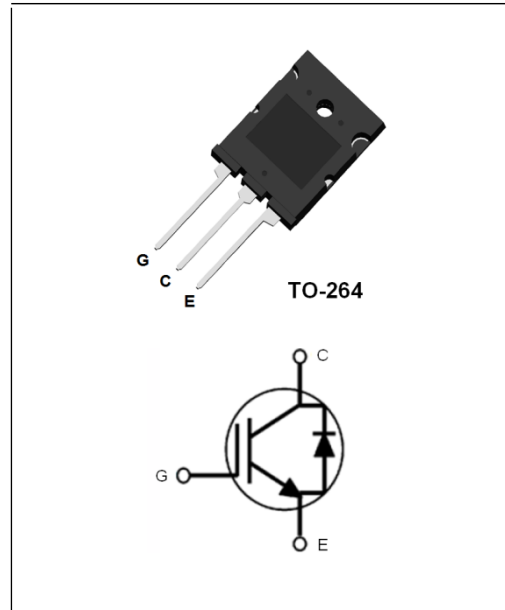
## 1200V 75A NPT IGBT

### Description

The device is designed by advanced NPT technology process. This IGBT offer low conduction and switching losses. This IGBT have excellent quality for application such as UPS, inverter, AC&DC motor controls and other switching applications.

### Features

- NPT Technology
- $V_{CE(sat)}=3.0V @ I_C=75A$
- $t_{rr}=67ns$ (typ.)
- High Speed Switching & Low Power Loss
- High Input Impedance



### Applications

- UPS, Inverter, Welder, AC&DC motor controls

### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit	
$V_{CES}$	Collector to Emitter Voltage	1200	V	
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V	
$I_C$	Collector Current	$T_C=25^\circ C$	120	A
		$T_C=100^\circ C$	75	A
$I_{CM}$	Pulsed Collector Current	225	A	
$I_F$	Diode Continuous Forward Current	$T_C=100^\circ C$	30	A
$I_{FM}$	Diode Maximum Forward Current	180	A	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ C$	480	W
		$T_C=100^\circ C$	190	W
$T_J$	Operating Junction Temperature Range	-55~+150	$^\circ C$	
$T_{STG}$	Storage Temperature Range	-55~+150	$^\circ C$	

### Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$ (IGBT)	Thermal Resistance, Junction to case for IGBT	0.26	$^\circ C/W$
$R_{th(J-C)}$ (Diode)	Thermal Resistance, Junction to case for Diode	0.65	$^\circ C/W$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	26	$^\circ C/W$

## Electrical Characteristics of IGBT @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	1200	-	-	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75A, V_{GE}=15V$	-	3.0	-	V
		$I_C=75A, V_{GE}=15V, T_C=125\text{ }^\circ\text{C}$	-	4.2	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=250\mu A$	4.5	5.8	6.8	V
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	1	mA
$I_{GES}$	Gate to Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V$	-	-	$\pm 250$	nA

## Electrical Characteristics of Diode @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=30A$	-	2.7	4.0	V
		$I_F=30A, T_C=125\text{ }^\circ\text{C}$	-	2.0	-	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F=30A, di/dt=-220A/\mu s$	-	67	-	ns
$I_{rr}$	Diode Peak Reverse Recovery Current		-	8.0	-	A
$Q_{rr}$	Diode Reverse Recovery Charge		-	185	-	nC

## Switching Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on Delay Time	$I_C=75A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega$ Inductive Load, $T_C=25\text{ }^\circ\text{C}$	-	50	-	ns	
$t_r$	Rising Time		-	158	-	ns	
$t_{d(off)}$	Turn-off Delay Time		-	242	-	ns	
$t_f$	Falling Time		-	30	-	ns	
$E_{on}$	Turn-on Switching Loss		-	6.3	-	mJ	
$E_{off}$	Turn-off Switching Loss		-	1.2	-	mJ	
$E_{ts}$	Total Switching Loss		-	7.5	-	mJ	
$t_{d(on)}$	Turn-on Delay Time		$I_C=75A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega$ Inductive Load, $T_C=125\text{ }^\circ\text{C}$	-	49	-	ns
$t_r$	Rising Time			-	150	-	ns
$t_{d(off)}$	Turn-off Delay Time			-	263	-	ns
$t_f$	Falling Time			-	48	-	ns
$E_{on}$	Turn-on Switching Loss			-	8.4	-	mJ
$E_{off}$	Turn-off Switching Loss	-		2.9	-	mJ	
$E_{ts}$	Total Switching Loss	-		11.3	-	mJ	
$C_{ies}$	Input Capacitance	$V_{GE}=0V, V_{CE}=30V, f=1.0MHz$	-	8330	-	pF	
$C_{res}$	Reverse Transfer Capacitance		-	140	-	pF	
$C_{oes}$	Output Capacitance		-	320	-	pF	
$Q_g$	Total Gate Charge	$I_C=75A, V_{CC}=600V, V_{GE}=15V$	-	37	-	nC	
$Q_{ge}$	Gate to Emitter Charge		-	160	-	nC	
$Q_{gc}$	Gate to Collector Charge		-	332	-	nC	
$t_{sc}$	Short Circuit Withstand Time		$V_{CC}=600V, V_{GE}=15V$	10	-	-	us

**Package Dimensions**

**TO-264**

(Dimensions in Millimeters)

